



PTO/SB/08A (10-01)

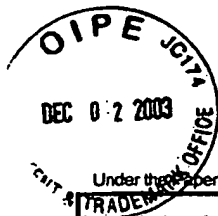
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/614,160
				Filing Date	July 8, 2003
				First Named Inventor	John T. Moore, et al.
				Art Unit	4848 2827
				Examiner Name	Not Yet Assigned V. Nguyen
Sheet	1	of	11	Attorney Docket Number	M4065.0715/P715

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code² (if known)			
W	AA	2002/0000666	1/3/2002	Kozicki et al.	
W	AB	2002/0072188	6/13/2002	Gilton	
W	AC	2002/0106849	08/08/2002	Moore	
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		Examiner Name	Not Yet Assigned V.N. Nguyen
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		Attorney Docket Number	M4065.0715/P715

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				Art Unit	4818 2827
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	AE4	6,487,106	11/26/2002	Kozicki	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ² -Number ³ -Kind Code ⁵ (if known)				
W	BA	56126916	10/19981	Akira et al.		
W	BB	WO 97/48032	12/18/1997	Kozicki et al.		
W	BC	WO 99/28914	06/10/1999	Kozicki et al.		
W	BD	WO 00/48196	08/17/2000	Kozicki et al.		
W	BE	WO 02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	V. Nguyen	Date Considered	3/31/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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			Group Art Unit	4810-2827	
			Examiner Name	Not Yet Assigned V. Nguyen	
Sheet	4	of	11	Attorney Docket Number	M4065.0715/P715

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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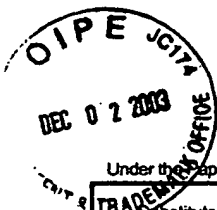
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